



DMN6017SFV

PowerDI3333-8 (Type UX)

Product Summary

BV _{DSS}	R _{DS(ON)} max	I _D max T _C = +25°C		
	18mΩ @ V _{GS} = 10V	35A		
60V	$20m\Omega @ V_{GS} = 4.5V$	34A		

Description and Applications

This MOSFET is designed to minimize the on-state resistance (R_{DS(ON)}) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Backlighting
- **Power Management Functions**
- **DC-DC Converters**

Features and Benefits

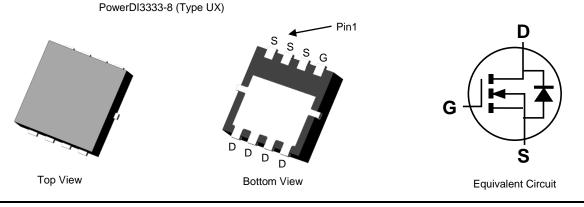
- Low R_{DS(ON)} Ensures on state losses are minimized
- Small form factor thermally efficient package enables higher density end products

60V N-CHANNEL ENHANCEMENT MODE MOSFET

- Occupies just 33% of the board area occupied by SO-8 enabling smaller end product
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

Mechanical Data

- Case: PowerDI[®]3333-8 (Type UX)
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections Indicator: See Diagram
- Terminals: Finish Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 3
- Weight: 0.030 grams (Approximate)



Ordering Information (Note 4)

	Part Number	Case	Packaging			
	DMN6017SFV-7	PowerDI3333-8 (Type UX)	2,000/Tape & Reel			
DMN6017SFV-13 PowerDI3333-8 (Type UX) 3,000/Tape & Ree		3,000/Tape & Reel				
Notes:	Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.					

2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.

3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/.

Marking Information



N67 = Product Type Marking Code YYWW = Date Code Marking \overline{YY} = Last Two Digits of Year (ex: 18 = 2018) WW = Week Code (01 to 53)

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Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	V _{DSS}	60	V	
Gate-Source Voltage		V _{GSS}	±20	V
Continuous Drain Current (Note 7) V _{GS} = 10V	$T_{C} = +25^{\circ}C$ $T_{C} = +70^{\circ}C$	ID	35 28	А
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)		I _{DM}	140	А
Maximum Continuous Body Diode Forward Current (Note 7)		Is	20	А
Pulsed Body Diode Forward Current (10µs Pulse, Duty Cycle = 1%)	I _{SM}	140	А	
Avalanche Current, L = 0.1mH (Note 8)	I _{AS}	25	А	
Avalanche Energy, L = 0.1mH (Note 8)		E _{AS}	32	mJ

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)		PD	1.0	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	126	°C/W
Total Power Dissipation (Note 6)		PD	2.0	W
Thermal Resistance, Junction to Ambient (Note 6) Steady State		$R_{\theta JA}$	62	°C/W
Thermal Resistance, Junction to Case (Note 7)		R _θ JC	3.7	C/W
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

			_				
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 9)		-					
Drain-Source Breakdown Voltage	BV _{DSS}	60	—	—	V	$V_{GS} = 0V, I_D = 250 \mu A$	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1	μA	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	—	—	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 9)							
Gate Threshold Voltage	V _{GS(TH)}	1	—	3	V	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	
Static Drain-Source On-Resistance			12	18	mΩ	$V_{GS} = 10V, I_D = 6A$	
	R _{DS(ON)}	_	13	20	11152	$V_{GS} = 4.5V, I_D = 4A$	
Diode Forward Voltage	V _{SD}		0.7	1	V	$V_{GS} = 0V, I_S = 1A$	
DYNAMIC CHARACTERISTICS (Note 10)							
Input Capacitance	Ciss		2711		рF		
Output Capacitance	Coss	_	152		pF	V _{DS} = 15V, V _{GS} = 0V, f = 1MHz	
Reverse Transfer Capacitance	C _{rss}		126		рF		
Gate Resistance	Rg		1.4	—	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge (V _{GS} = 4.5V)	Qg	_	26		nC		
Total Gate Charge (V _{GS} = 10V)	Qg		55		nC	V _{DS} = 48V, I _D = 6A	
Gate-Source Charge	Q _{gs}	_	6.2		nC	VDS = 48V, ID = 6A	
Gate-Drain Charge	Q _{gd}		8.5	—	nC		
Turn-On Delay Time	t _{D(ON)}	_	4.9	—	ns		
Turn-On Rise Time	t _R	_	5.4	_	ns	$V_{DD} = 30V, V_{GS} = 10V,$ $R_G = 3.3\Omega, I_D = 6A$	
Turn-Off Delay Time	t _{D(OFF)}	_	38.2	_	ns		
Turn-Off Fall Time	tF		11	_	ns		
Reverse Recovery Time	t _{RR}	_	16.6	_	ns		
Reverse Recovery Charge	Q _{RR}		10.3	_	nC	$I_F = 6A$, di/dt = 100A/µs	

Notes:

Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1-inch square copper plate.

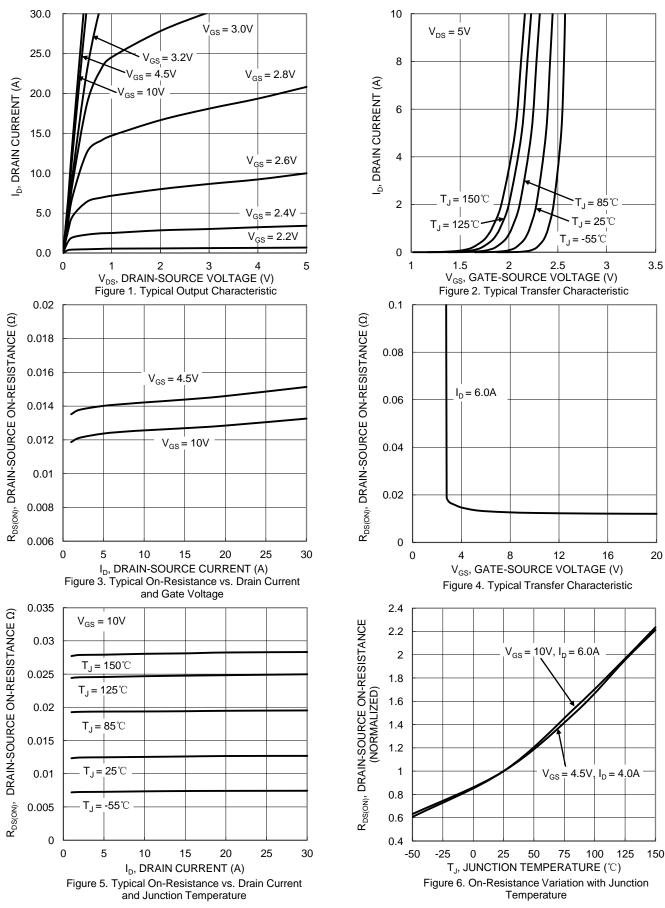
7. Thermal resistance from junction to soldering point (on the exposed drain pad).

8. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep $T_J = +25^{\circ}C$.

Short duration pulse test used to minimize self-heating effect.
Guaranteed by design. Not subject to product testing.

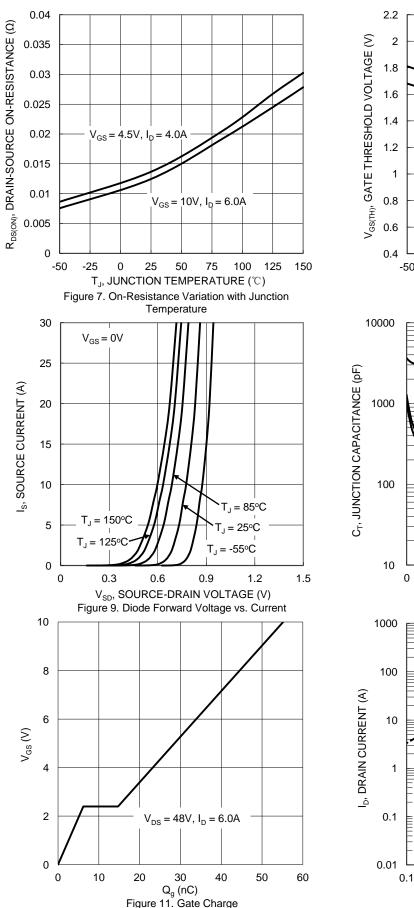


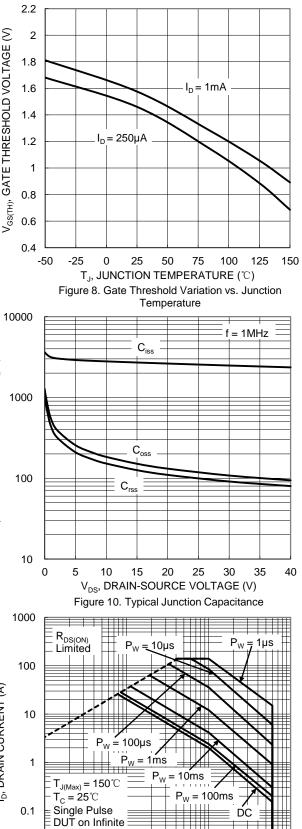
DMN6017SFV











Heatsink $V_{GS} = 10V$

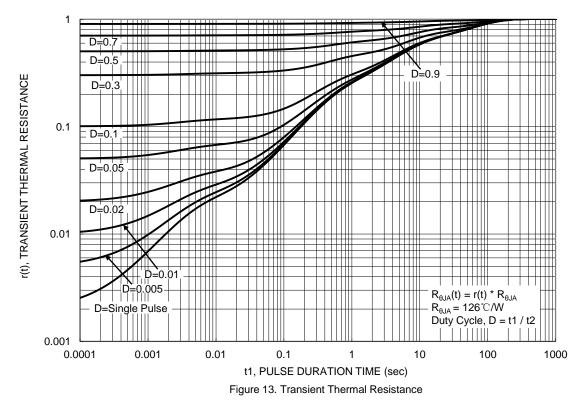
1 10 V_{DS}, DRAIN-SOURCE VOLTAGE (V)

Figure 12. SOA, Safe Operation Area

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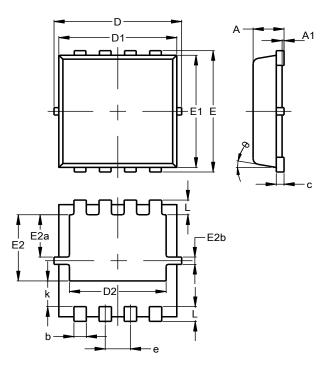




Package Outline Dimensions

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)

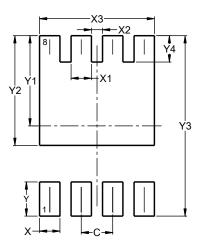


PowerDI3333-8						
(Type UX)						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05				
b	0.25	0.40	0.32			
c	0.10	0.25	0.15			
D	3.20	3.20 3.40 3.30				
D1	2.95	3.15	3.05			
D2	2.30	2.70	2.50			
Е	3.20	3.40	3.30			
E1	2.95	3.15	3.05			
E2	1.60	2.00	1.80			
E2a	0.95	1.35	1.15			
E2b	0.10	0.30	0.20			
е	0.65 BSC					
k	0.50	0.90	0.70			
L	0.30	0.50	0.40			
θ	0°	12°	10°			
All	All Dimensions in mm					

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

PowerDI3333-8 (Type UX)



Dimensions	Value (in mm)			
С	0.650			
Х	0.420			
X1	0.420			
X2	0.230			
X3	2.370			
Y	0.700			
Y1	1.850			
Y2	2.250			
Y3	3.700			
Y4	0.540			



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